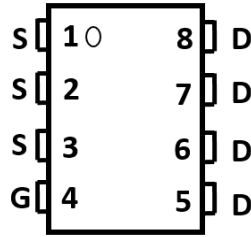
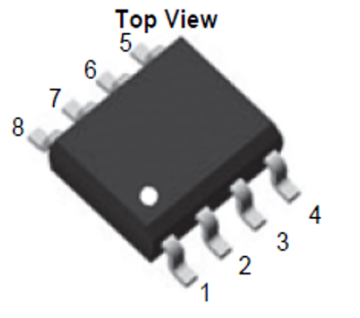
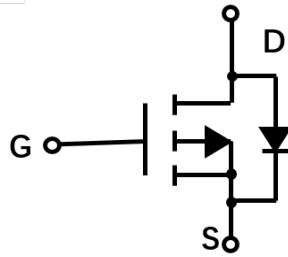


P-Channel Enhancement Mode Field Effect Transistor



SOP-8



Product Summary

- V_{DS} -30V
- I_D -10A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <20.8mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <27.8mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-30	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ\text{C}$ @ Steady State	-10
		$T_A=70^\circ\text{C}$ @ Steady State	-8
Pulsed Drain Current ^A	I_{DM}	-50	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	3.0	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	42	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS4435A	F2	Q4435A	4000	8000	64000	13" reel



YJS4435A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V, T _C =25°C			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.0	-1.5	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D =-10A		15.3	20.8	mΩ
		V _{GS} = -4.5V, I _D =-5.0A		20.8	27.8	
Diode Forward Voltage	V _{SD}	I _S =-10A, V _{GS} =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I _S				-10	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHZ		1500		pF
Output Capacitance	C _{oss}			178		
Reverse Transfer Capacitance	C _{rss}			146		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-6.0A		28.7		nC
Gate Source Charge	Q _{gs}			5.5		
Gate Drain Charge	Q _{gd}			5.4		
Reverse Recovery Charge	Q _{rr}	I _F = -9A, di/dt=500A/us		6.0		
Reverse Recovery Time	t _{rr}			14		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DS} =-15V, I _D =-6.0A, R _{GEN} =2.5Ω		10		ns
Turn-on Rise Time	t _r			44		
Turn-off Delay Time	t _{D(off)}			54		
Turn-off Fall Time	t _f			59		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R_{θJA} is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. R_{θJL} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

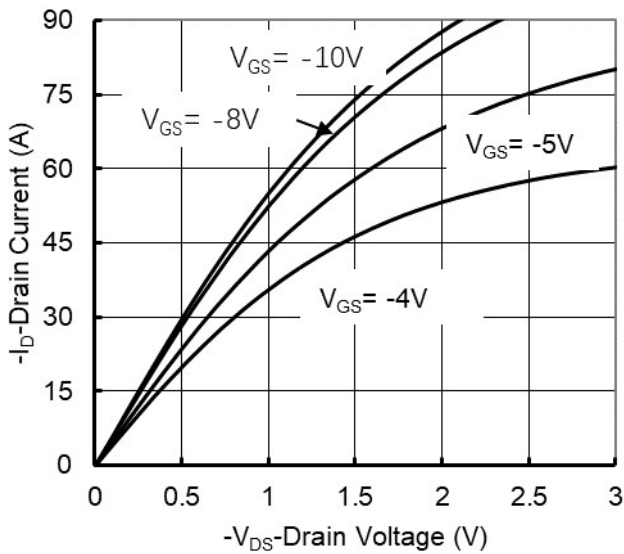


Figure 1. Output Characteristics

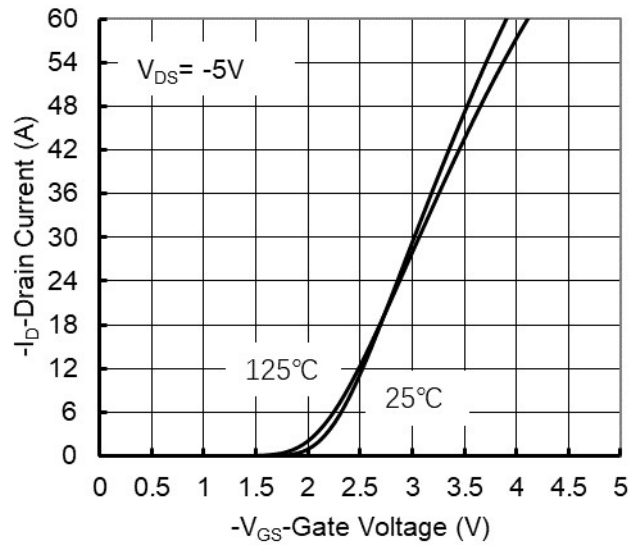


Figure 2. Transfer Characteristics

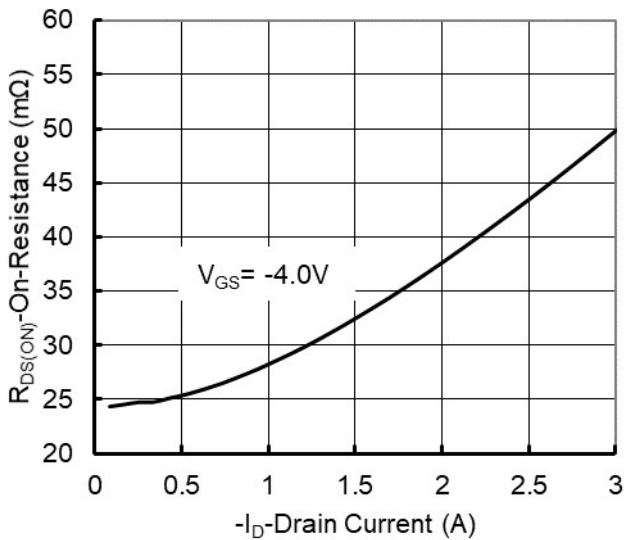


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

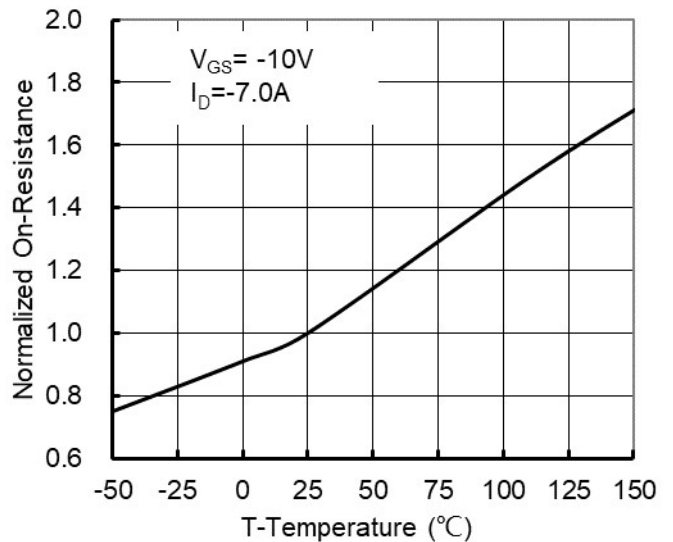


Figure 4. On-Resistance vs. Junction Temperature

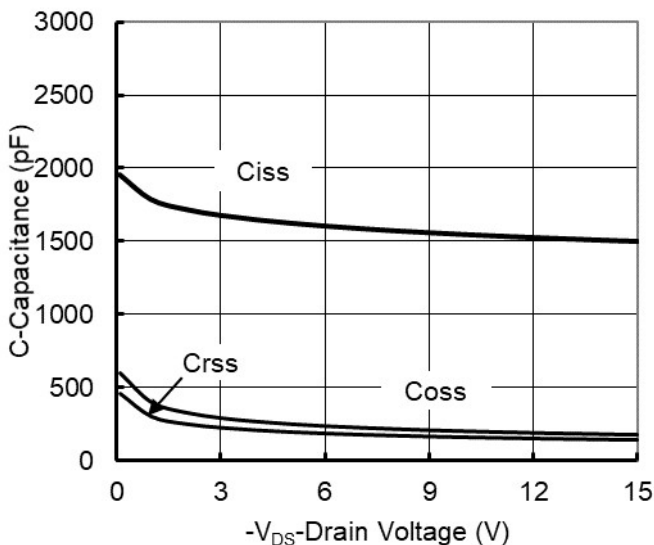


Figure 5. Capacitance Characteristics

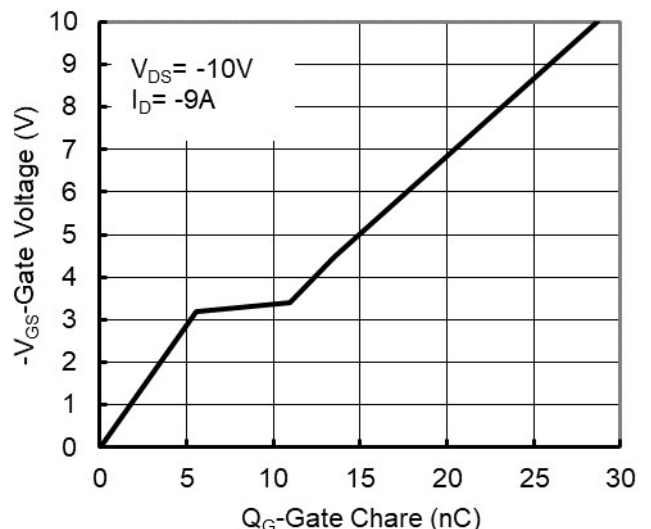


Figure 6. Gate Charge

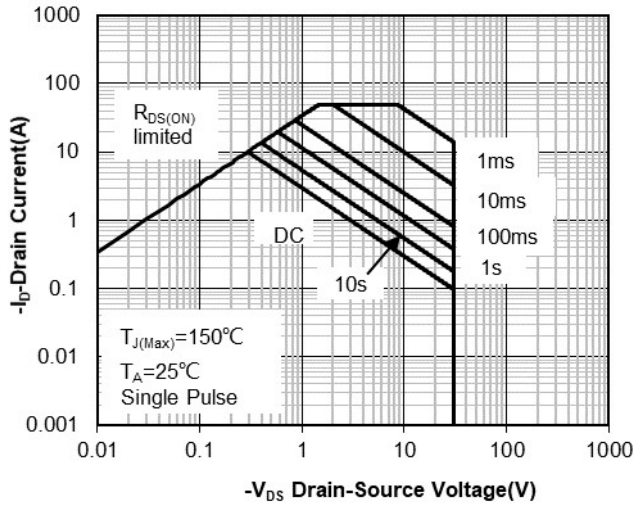


Figure 7. Safe Operation Area

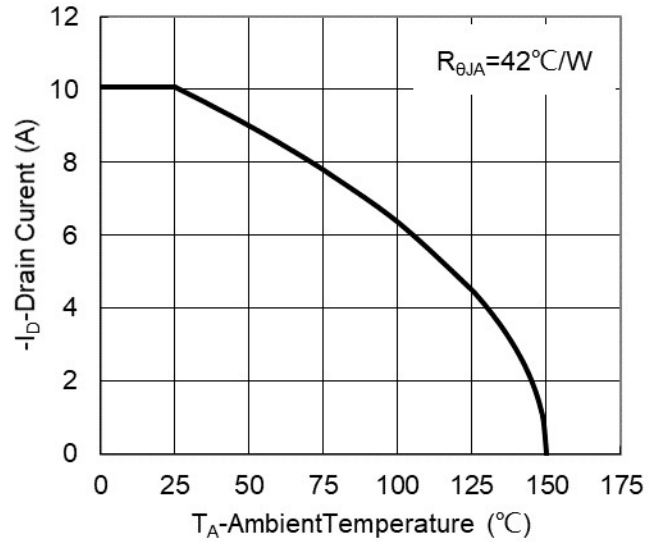


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

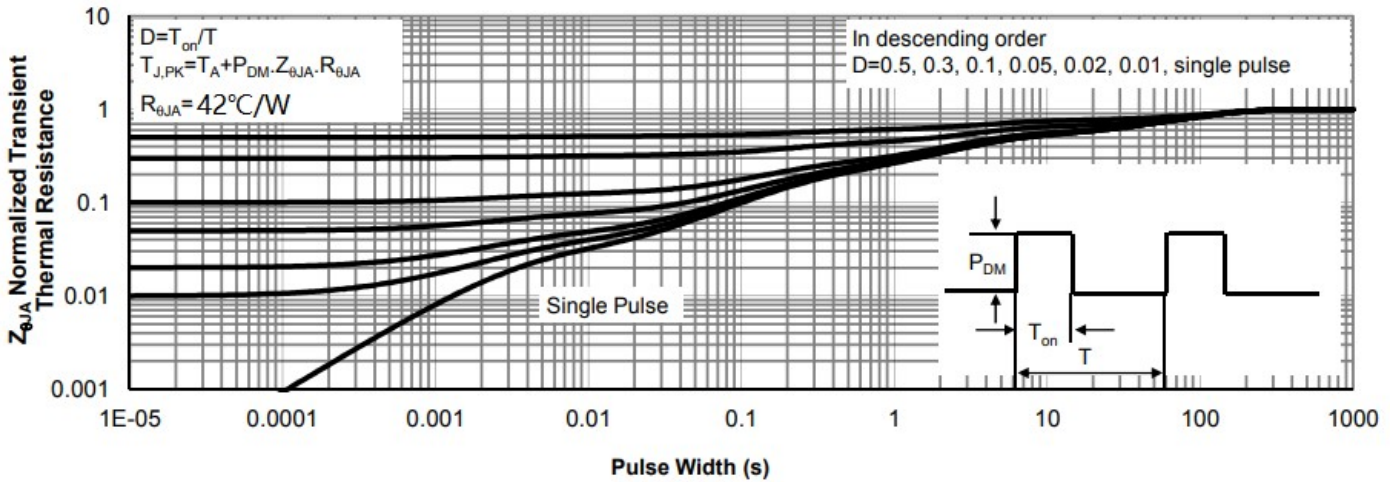


Figure 9. Normalized Maximum Transient Thermal Impedance



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

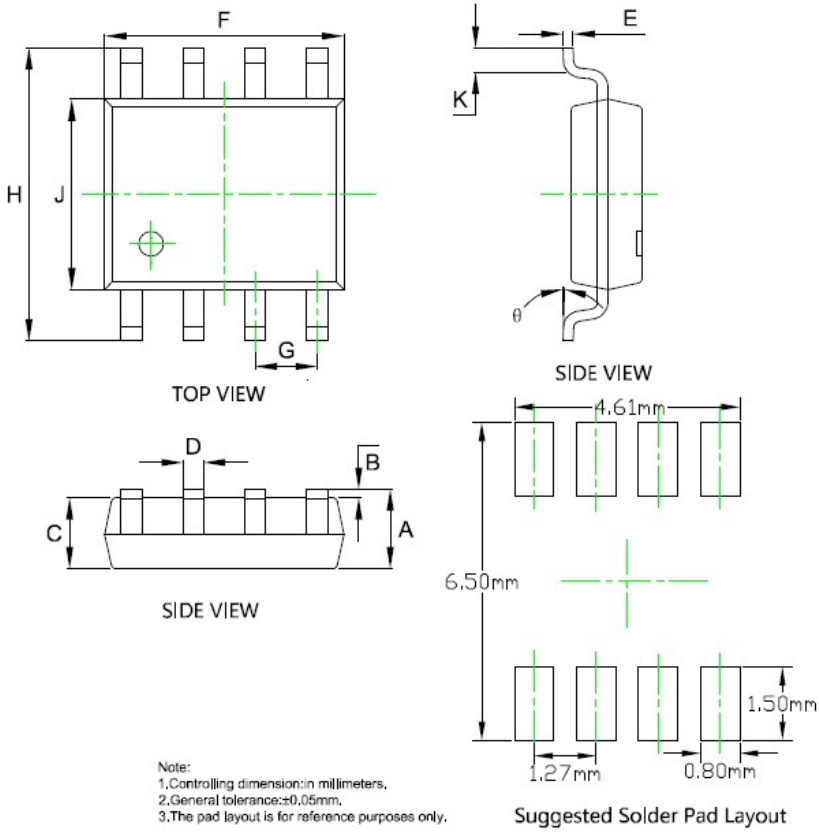


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



YJS4435A

■ SOP-8 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
θ	0°	8°	0°	8°



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